

Claims

- [c1] 1. A stress relieving method for a wafer, comprising the steps of:
providing a wafer with a dielectric layer thereon, wherein the wafer is divided into a first area and a second area such that at least no circuits are formed on the dielectric layer within the first area;
forming a plurality of first openings in the dielectric layer within the first area; and
forming a first material layer over the wafer, wherein the upper surface of the first material layer has pits at locations over the first openings.
- [c2] 2. The stress relieving method of claim 1, wherein the first area comprises a scribe line.
- [c3] 3. The stress relieving method of claim 1, wherein the second area comprises a region for forming a die.
- [c4] 4. The stress relieving method of claim 3, wherein the first area comprises a scribe line.
- [c5] 5. The stress relieving method of claim 1, wherein the first area and the second area are both regions for forming a die.

- [c6] 6. The stress relieving method of claim 1, wherein the step of forming first openings in the dielectric layer within the first area further comprises forming a plurality of second openings in the first dielectric layer within the second area at the same time and then depositing material into the second openings to form a plurality of second material layers.
- [c7] 7. The stress relieving method of claim 1, wherein the first opening is not deep enough to expose a film layer underneath the dielectric layer.
- [c8] 8. The stress relieving method of claim 1, wherein the first opening exposes a film layer underneath the dielectric layer.
- [c9] 9. The stress relieving method of claim 1, wherein the first material layer is fabricated from a dielectric material or a metal material.
- [c10] 10. A stress relieving method for a wafer, comprising the steps of:
providing a wafer with a dielectric layer thereon, wherein the wafer is divided into a first area and a second area such that no circuits are formed within the first area;
forming a first material layer over the wafer; and
removing a portion of the first material layer within the

first area to form a plurality of first openings.

[c11] 11. The stress relieving method of claim 10, wherein the first area comprises a scribe line.

[c12] 12. The stress relieving method of claim 10, wherein the second area comprises a region for forming a die.

[c13] 13. The stress relieving method of claim 12, wherein the first area comprises a scribe line.

[c14] 14. The stress relieving method of claim 10, wherein the first area and the second area are both regions for forming a die.

[c15] 15. The stress relieving method of claim 10, wherein the first opening is not deep enough to expose the dielectric layer.

[c16] 16. The stress relieving method of claim 10, wherein the first opening exposes the dielectric layer.

[c17] 17. The stress relieving method of claim 9, wherein before forming the second dielectric layer over the wafer, further comprises:
forming a plurality of second openings in the dielectric layer within the second area; and
depositing material into the second openings to form a plurality of second material layers.

[c18] 18. The stress relieving method of claim 10, wherein the first material layer is fabricated from a dielectric material or a metal material.